

Search Notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3799	(438/694).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
L2	387	(438/695).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
L3	1017	(438/700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
L4	876	(438/702).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
L5	16	hdpcvd and etch\$3 with he	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:10
L6	62	hdpcvd and etch\$3 with hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:10
L7	21	hdpcvd and etch\$3 with hydrogen with (argon or nitrogen or helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:10
L8	22	high adj density adj plasma with cvd and etch\$3 adj hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:11
L9	3	known same radio adj frequency near inductively adj coupled adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:11

L10	5	known with etch adj rate with bias adj power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:11
S1	15	hdpcvd and etch\$3 with he	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:10
S2	47	hdpcvd and etch\$3 with hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:10
S3	18	hdpcvd and etch\$3 with hydrogen with (argon or nitrogen or helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:10
S4	0	hdpcvd and etch\$3 adj hydrogen with (argon or nitrogen or helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 17:47
S5	0	hdpcvd and etch\$3 adj hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 17:47
S6	380	cvd and etch\$3 adj hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 17:48
S7	155	plasma with cvd and etch\$3 adj hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 17:48
S8	19	high adj density adj plasma with cvd and etch\$3 adj hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:11
S9	92	high adj density adj plasma with cvd and etch\$3 with "h.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 17:55

S10	8	high adj density adj plasma with cvd and etch\$3 near "h.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:30
S11	1	"6596654".PN.	USPAT; USOCR	OR	ON	2005/04/08 18:00
S12	1	"6395150".PN.	USPAT; USOCR	OR	ON	2005/04/08 18:10
S13	1	"6335288".PN.	USPAT; USOCR	OR	ON	2005/04/08 18:17
S14	1	"6203863".PN.	USPAT; USOCR	OR	ON	2005/04/08 18:18
S15	1	"6197705".PN.	USPAT; USOCR	OR	ON	2005/04/08 18:20
S16	0	high adj density adj plasma with cvd and etch\$3 near "h.sub.2" with helium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:30
S17	0	high adj density adj plasma with cvd and etch\$3 with "h.sub.2" with helium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:31
S18	9	high adj density adj plasma with cvd and etch\$3 with "h.sub.2" with he	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:55
S19	0	well adj known with radio adj frequency near inductively adj coupled adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:56
S20	0	well adj known same radio adj frequency near inductively adj coupled adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:56
S21	0	well with known same radio adj frequency near inductively adj coupled adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:56
S22	3	known same radio adj frequency near inductively adj coupled adj plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:11

S23	0	known with RF-ICp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:57
S24	3	known same RF-ICp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 19:57
S25	7	RF-ICp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 20:00
S26	0	well adj known with etch adj rate with bias adj power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 20:01
S27	4	known with etch adj rate with bias adj power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 02:11
S28	0	well adj known same etch adj rate with bias adj power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 20:03
S29	15	well adj known same etch adj rate with power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/08 20:03
S30	3734	(438/694).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
S31	373	(438/695).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
S32	930	(438/700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10

S33	864	(438/702).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 02:10
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